SN65C3238E, SN75C3238E
3-V TO 5.5-V MULTICHANNEL RS-232 LINE DRIVERS/RECEIVERS WITH ±15-kV ESD (HBM) PROTECTION

SLLS726 – MAY 2006

PRODUCT PREVIEW

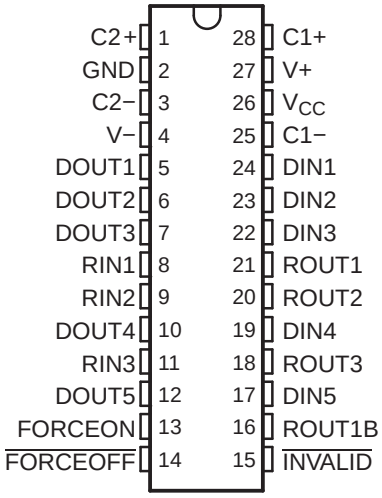
FEATURES

- **RS-232 Bus-Pin ESD Protection Exceeds ±15 kV Using Human-Body Model (HBM)**
- **Meet or Exceed the Requirements of TIA/EIA-232-F and ITU v.28 Standards**
- **Operate With 3-V to 5.5-V V_{CC} Supply**
- **Operate up to 1000 kbit/s**
- **Five Drivers and Three Receivers**
- **Auto-Powerdown Plus Feature Enables Flexible Power-Down Mode**
- **Low Standby Current . . . 1 μA Typical**
- **External Capacitors . . . 4 × 0.1 μF**
- **Accept 5-V Logic Input With 3.3-V Supply**
- **Always-Active Noninverting Receiver Output (ROUT1B)**
- **ESD Protection for RS-232 Interface Pins**
  - **– ±15 kV – Human-Body Model (HBM)**
  - **– ±8 kV – IEC61000-4-2, Contact Discharge**
  - **– ±15 kV – IEC61000-4-2, Air-Gap Discharge**

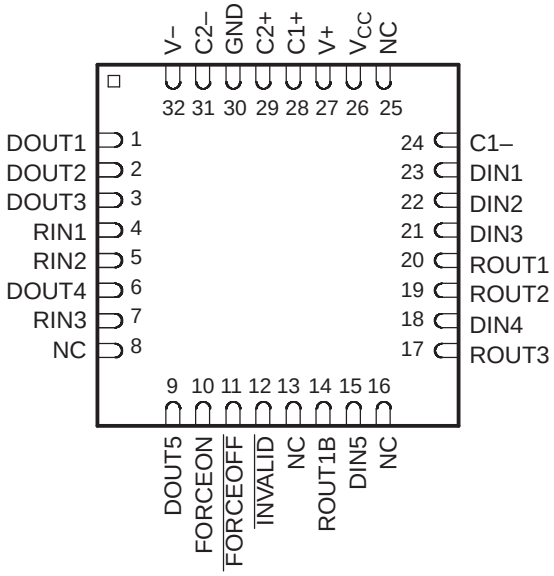
APPLICATIONS

- **Battery-Powered Systems**
- **PDAs**
- **Notebooks**
- **Subnotebooks**
- **Laptops**
- **Palmtop PCs**
- **Hand-Held Equipment**
- **Modems**
- **Printers**

DB, DW, OR PW PACKAGE
(TOP VIEW)



RHB PACKAGE
(TOP VIEW)



DESCRIPTION/ORDERING INFORMATION

The SN65C3238E and SN75C3238E consist of five line drivers, three line receivers, and a dual charge-pump circuit with ±15-kV ESD (HBM) protection on the driver output (DOUT) and receiver input (RIN) terminals. The devices meet the requirements of TIA/EIA-232-F and provide the electrical interface between notebook and subnotebook computer applications. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. In addition, the devices include an always-active noninverting output (ROUT1B), which allows applications using the ring indicator to transmit data while the device is powered down. These devices operate at data signaling rates up to 1000 kbit/s.

DESCRIPTION/ORDERING INFORMATION (CONTINUED)

Flexible control options for power management are featured when the serial port and driver inputs are inactive. The auto-powerdown plus feature functions when FORCEON is low and $\overline{\text{FORCEOFF}}$ is high. During this mode of operation, if the devices do not sense valid signal transitions on all receiver and driver inputs for approximately 30 s, the built-in charge pump and drivers are powered down, reducing the supply current to 1 µA. By disconnecting the serial port or placing the peripheral drivers off, auto-powerdown plus occurs if there is no activity in the logic levels for the driver inputs. Auto-powerdown plus can be disabled when FORCEON and $\overline{\text{FORCEOFF}}$ are high. With auto-powerdown plus enabled, the devices activate automatically when a valid signal is applied to any receiver or driver input. $\overline{\text{INVALID}}$ is high (valid data) if any receiver input voltage is greater than 2.7 V or less than –2.7 V, or has been between –0.3 V and 0.3 V for less than 30 µs. $\overline{\text{INVALID}}$ is low (invalid data) if all receiver input voltages are between –0.3 V and 0.3 V for more than 30 µs. Refer to Figure 5 for receiver input levels.

ORDERING INFORMATION

T_A	PACKAGE(1)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
0°C to 70°C	SSOP – DB	Tube of 50	SN75C3238EDB	75C3238E
		Reel of 2000	SN75C3238EDBR	
	TSSOP – PW	Tube of 50	SN75C3238EPW	Preview
		Reel of 2000	SN75C3238EPWR	
	SOIC – DW	Tube of 50	SN75C3238EDW	75C3238E
		Reel of 2000	SN75C3238EDWR	
	QFN – RHB	Reel of 2000	SN75C3238ECRHBR	Preview
–40°C to 85°C	SSOP – DB	Tube of 50	SN65C3238EDB	65C3238E
		Reel of 2000	SN65C3238EDBR	
	TSSOP – PW	Tube of 50	SN65C3238EPW	Preview
		Reel of 2000	SN65C3238EPWR	
	SOIC – DW	Tube of 50	SN65C3238EDW	65C3238E
		Reel of 2000	SN65C3238EDWR	
	QFN – RHB	Reel of 2000	SN65C3238EIRHBR	Preview

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

PRODUCT PREVIEW

FUNCTION TABLES

Each Driver(1)

INPUTS				OUTPUT	DRIVER STATUS
DIN	FORCEON	$\overline{\text{FORCEOFF}}$	TIME ELAPSED SINCE LAST RIN OR DIN TRANSITION	DOUT	
X	X	L	X	Z	Powered off
L	H	H	X	H	Normal operation with auto-powerdown plus disabled
H	H	H	X	L	
L	L	H	<30 s	H	Normal operation with auto-powerdown plus enabled
H	L	H	<30 s	L	
L	L	H	>30 s	Z	Powered off by auto-powerdown plus feature
H	L	H	>30 s	Z	

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

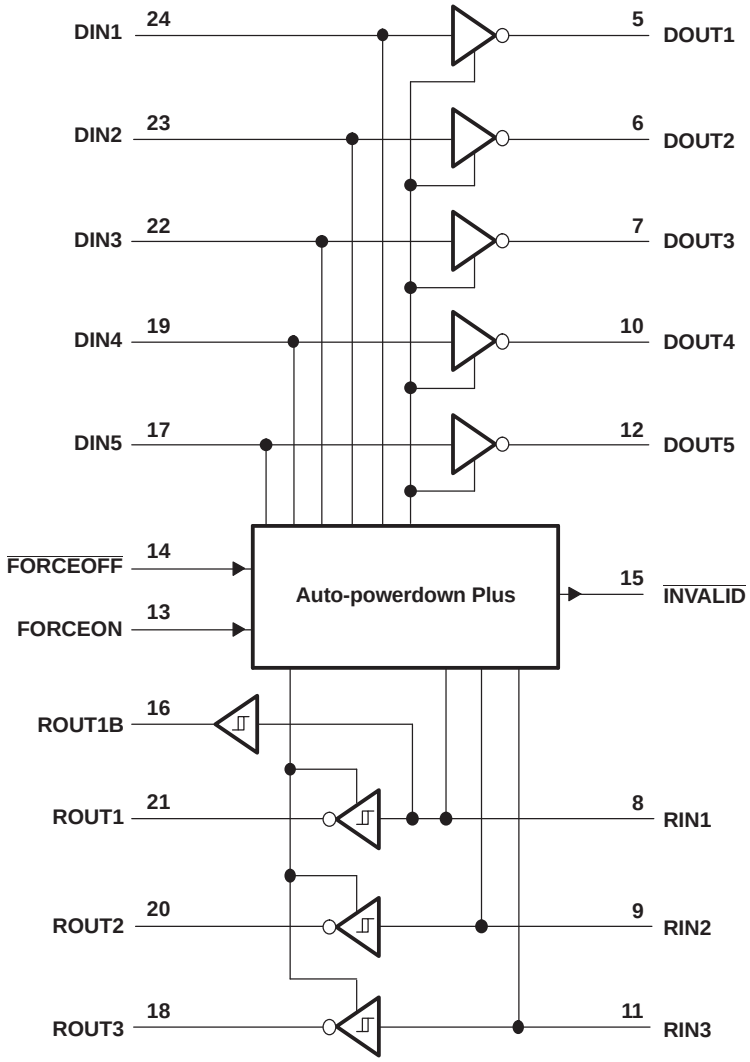
Each Receiver(1)

INPUTS				OUTPUTS		RECEIVER STATUS
RIN1	RIN2–RIN3	$\overline{\text{FORCEOFF}}$	TIME ELAPSED SINCE LAST RIN OR DIN TRANSITION	ROUT1B	ROUT2 AND ROUT3	
L	X	L	X	L	Z	Powered off while ROUT1B is active
H	X	L	X	H	Z	
L	L	H	<30 s	L	H	Normal operation with auto-powerdown plus disabled/enabled
L	H	H	<30 s	L	L	
H	L	H	<30 s	H	H	
H	H	H	<30 s	H	L	
Open	Open	H	<30 s	L	H	

(1) H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = input disconnected or connected driver off

PRODUCT PREVIEW

LOGIC DIAGRAM (POSITIVE LOGIC)



Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range(2)		–0.3	6	V
V+	Positive-output supply voltage range(2)		–0.3	7	V
V–	Negative-output supply voltage range(2)		0.3	–7	V
V+ – V–	Supply voltage difference(2)			13	V
V_I	Input voltage range	Driver ($\overline{\text{FORCEOFF}}$, FORCEON)	–0.3	6	V
		Receiver	–25	25	
V_O	Output voltage range	Driver	–13.2	13.2	V
		Receiver ($\overline{\text{INVALID}}$)	–0.3	V_{CC} + 0.3	
θ_{JA}	Package thermal impedance(3)(4)	DB package		62	°C/W
		DW package		46	
		PW package		62	
		RHB package		TBD	
T_J	Operating virtual junction temperature			150	°C
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to network GND.
(3) Maximum power dissipation is a function of $T_J(max)$, θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) – T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
(4) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions(1)

See Figure 6

				MIN	NOM	MAX	UNIT
	Supply voltage		V_{CC} = 3.3 V	3	3.3	3.6	V
			V_{CC} = 5 V	4.5	5	5.5	
V_{IH}	Driver and control high-level input voltage	DIN, $\overline{\text{FORCEOFF}}$, FORCEON	V_{CC} = 3.3 V	2		5.5	V
			V_{CC} = 5 V	2.4		5.5	
V_{IL}	Driver and control low-level input voltage	DIN, $\overline{\text{FORCEOFF}}$, FORCEON		0		0.8	V
V_I	Receiver input voltage			–25		25	V
T_A	Operating free-air temperature		SN75C3238E	0		70	°C
			SN65C3238E	–40		85	

(1) Testing supply conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.15 V; C1–C4 = 0.22 µF at V_{CC} = 3.3 V ± 0.3 V; and C1 = 0.047 µF and C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6)

PARAMETER			TEST CONDITIONS	MIN	TYP(2)	MAX	UNIT
I_I	Input leakage current	$\overline{\text{FORCEOFF}}$, FORCEON			±0.01	±1	µA
I_{CC}	Supply current (T_A = 25°C)	Auto-powerdown plus disabled	No load, $\overline{\text{FORCEOFF}}$ and FORCEON at V_{CC}		0.5	2	mA
		Powered off	No load, $\overline{\text{FORCEOFF}}$ at GND		1	10	µA
		Auto-powerdown plus enabled	No load, $\overline{\text{FORCEOFF}}$ at V_{CC}, FORCEON at GND, All RIN are open or grounded		1	10	

(1) Testing supply conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.15 V; C1–C4 = 0.22 µF at V_{CC} = 3.3 V ± 0.3 V; and C1 = 0.047 µF and C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

PRODUCT PREVIEW

DRIVER SECTION

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6)

PARAMETER		TEST CONDITIONS			MIN	TYP(2)	MAX	UNIT
V_{OH}	High-level output voltage	All DOUT at R_L = 3 kΩ to GND			5	5.4		V
V_{OL}	Low-level output voltage	All DOUT at R_L = 3 kΩ to GND			–5	–5.4		V
I_{IH}	High-level input current	$V_I = V_{CC}$				±0.01	±1	µA
I_{IL}	Low-level input current	V_I at GND				±0.01	±1	µA
I_{OS}	Short-circuit output current(3)	V_{CC} = 3.6 V,	V_O = 0 V			±35	±60	mA
		V_{CC} = 5.5 V,	V_O = 0 V			±40	±100	
r_o	Output resistance	V_{CC}, V+, and V– = 0 V,	V_O = ±2 V		300	10M		Ω
I_{OZ}	Output leakage current	$\overline{\text{FORCEOFF}}$ = GND	V_O = ±12 V,	V_{CC} = 3 V to 3.6 V			±25	µA
			V_O = ±10 V,	V_{CC} = 4.5 V to 5.5 V			±25	

(1) Testing supply conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.15 V; C1–C4 = 0.22 µF at V_{CC} = 3.3 V ± 0.3 V; and C1 = 0.047 µF and C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(3) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

Switching Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6)

PARAMETER		TEST CONDITIONS			MIN	TYP(2)	MAX	UNIT
	Maximum data rate (see Figure 1)	R_L = 3 kΩ, One DOUT switching	C_L = 1000 pF		250			kbit/s
			C_L = 250 pF,	V_{CC} = 3 V to 4.5 V	1000			
			C_L = 1000 pF,	V_{CC} = 4.5 V to 5.5 V	1000			
$t_{sk(p)}$	Pulse skew(3)	C_L = 150 pF to 2500 pF,	R_L = 3 kΩ to 7 kΩ,	See Figure 2		25		ns
SR(tr)	Slew rate, transition region (see Figure 1)	C_L = 150 pF to 1000 pF,	R_L = 3 kΩ to 7 kΩ,	V_{CC} = 3.3 V	18		150	V/µs

(1) Testing supply conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.15 V; C1–C4 = 0.22 µF at V_{CC} = 3.3 V ± 0.3 V; and C1 = 0.047 µF and C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(3) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

ESD Protection

PARAMETER	TEST CONDITIONS	TYP	UNIT
DOUT	HBM	±15	kV
	IEC 61000-4-2, Air-Gap Discharge	±15	
	IEC 61000-4-2, Contact Discharge	±8	

RECEIVER SECTION

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 6)

PARAMETER		TEST CONDITIONS	MIN	TYP(2)	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –1 mA	V_{CC} – 0.6	V_{CC} – 0.1		V
V_{OL}	Low-level output voltage	I_{OL} = 1.6 mA			0.4	V
V_{IT+}	Positive-going input threshold voltage	V_{CC} = 3.3 V		1.5	2.4	V
		V_{CC} = 5 V		1.8	2.4	
$V_{IT–}$	Negative-going input threshold voltage	V_{CC} = 3.3 V	0.6	1.2		V
		V_{CC} = 5 V	0.8	1.5		
V_{hys}	Input hysteresis ($V_{IT+} – V_{IT–}$)			0.3		V
I_{OZ}	Output leakage current (except ROUT1B)	$\overline{FORCEOFF}$ = 0 V		±0.05	±10	µA
r_i	Input resistance	V_I = ±3 V to ±25 V	3	5	7	kΩ

(1) Testing supply conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.15 V; C1–C4 = 0.22 µF at V_{CC} = 3.3 V ± 0.3 V; and C1 = 0.047 µF and C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

Switching Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TYP(2)	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	C_L = 150 pF, See Figure 3	150	ns
t_{PHL}	Propagation delay time, high- to low-level output	C_L = 150 pF, See Figure 3	150	ns
t_{en}	Output enable time	C_L = 150 pF, R_L = 3 kΩ, See Figure 4	200	ns
t_{dis}	Output disable time	C_L = 150 pF, R_L = 3 kΩ, See Figure 4	200	ns
$t_{sk(p)}$	Pulse skew(3)	See Figure 3	50	ns

(1) Testing supply conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.15 V; C1–C4 = 0.22 µF at V_{CC} = 3.3 V ± 0.3 V; and C1 = 0.047 µF and C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(3) Pulse skew is defined as $|t_{PLH} – t_{PHL}|$ of each channel of the same device.

ESD Protection

PARAMETER	TEST CONDITIONS	TYP	UNIT
RIN	HBM	±15	kV
	IEC 61000-4-2, Air-Gap Discharge	±15	
	IEC 61000-4-2, Contact Discharge	±8	

PRODUCT PREVIEW

AUTO-POWERDOWN PLUS SECTION

Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDITIONS	MIN	MAX	UNIT
$V_{T+(valid)}$	Receiver input threshold for $\overline{INVALID}$ high-level output voltage	FORCEON = GND, $\overline{FORCEOFF}$ = V_{CC}		2.7	V
$V_{T-(valid)}$	Receiver input threshold for $\overline{INVALID}$ high-level output voltage	FORCEON = GND, $\overline{FORCEOFF}$ = V_{CC}	–2.7		V
$V_{T(invalid)}$	Receiver input threshold for $\overline{INVALID}$ low-level output voltage	FORCEON = GND, $\overline{FORCEOFF}$ = V_{CC}	–0.3	0.3	V
V_{OH}	$\overline{INVALID}$ high-level output voltage	I_{OH} = –1 mA, FORCEON = GND, $\overline{FORCEOFF}$ = V_{CC}	V_{CC} – 0.6		V
V_{OL}	$\overline{INVALID}$ low-level output voltage	I_{OL} = 1.6 mA, FORCEON = GND, $\overline{FORCEOFF}$ = V_{CC}		0.4	V

Switching Characteristics

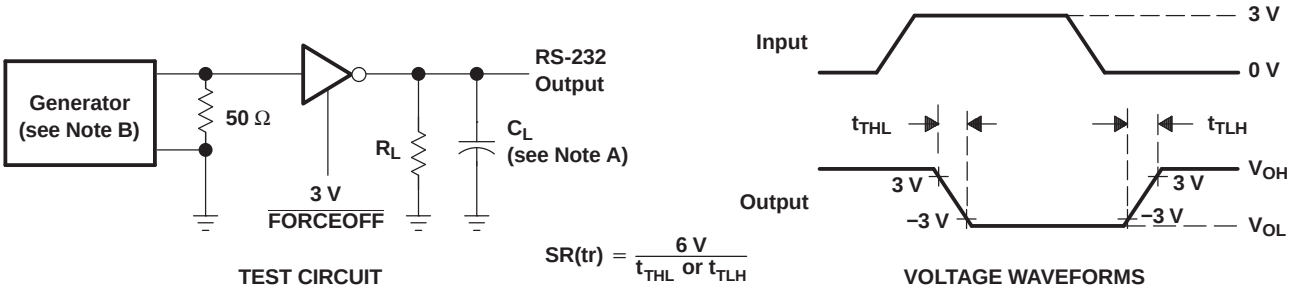
over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		MIN	TYP(1)	MAX	UNIT
t_{valid}	Propagation delay time, low- to high-level output		0.1		µs
$t_{invalid}$	Propagation delay time, high- to low-level output		50		µs
t_{en}	Supply enable time		25		µs
t_{dis}	Receiver or driver edge to auto-powerdown plus	15	30	60	s

(1) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

PRODUCT PREVIEW

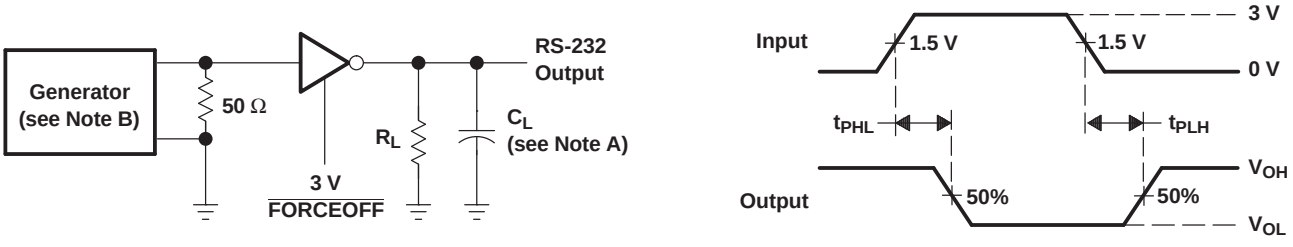
PARAMETER MEASUREMENT INFORMATION



A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

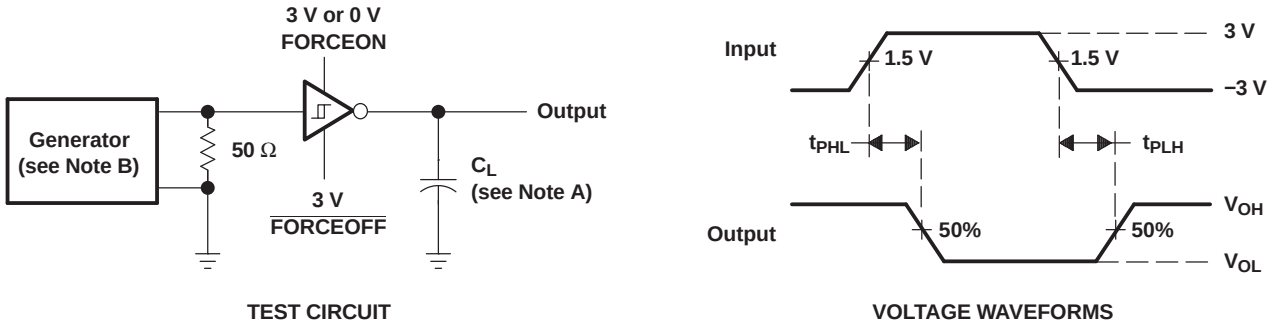
Figure 1. Driver Slew Rate



A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 2. Driver Pulse Skew



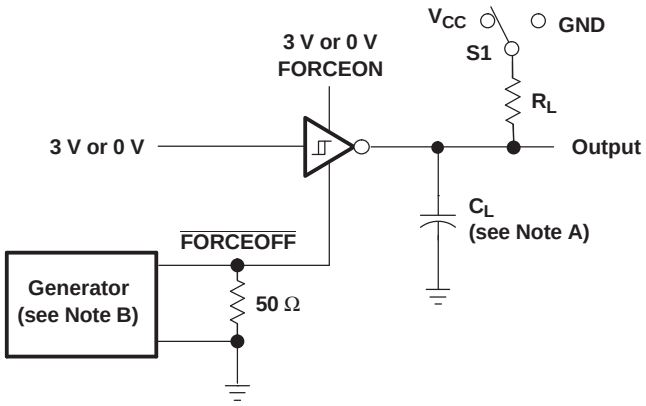
A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

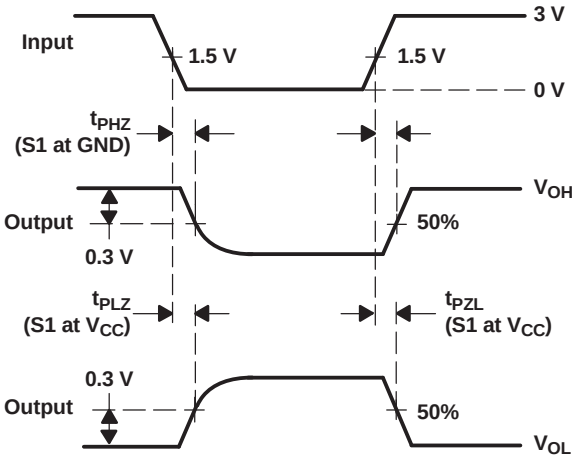
Figure 3. Receiver Propagation Delay Times

PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION (continued)



TEST CIRCUIT



VOLTAGE WAVEFORMS

A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

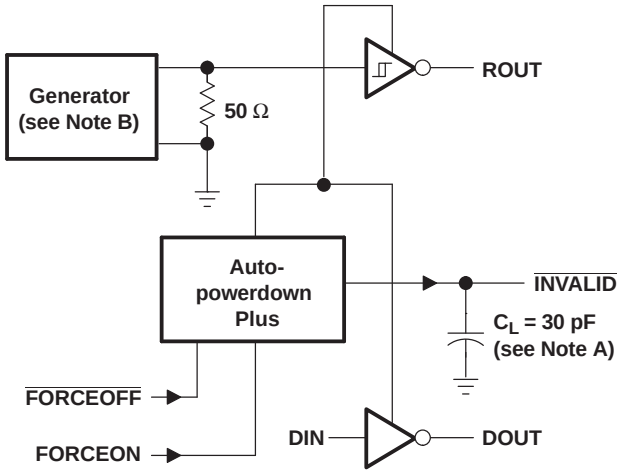
C. t_{PLZ} and t_{PHZ} are the same as t_{dis}.

D. t_{PZL} and t_{PZH} are the same as t_{en}.

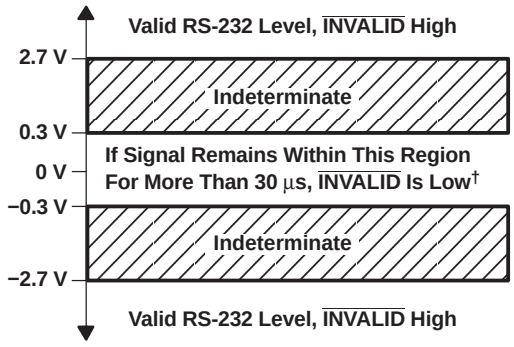
Figure 4. Receiver Enable and Disable Times

PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION (continued)

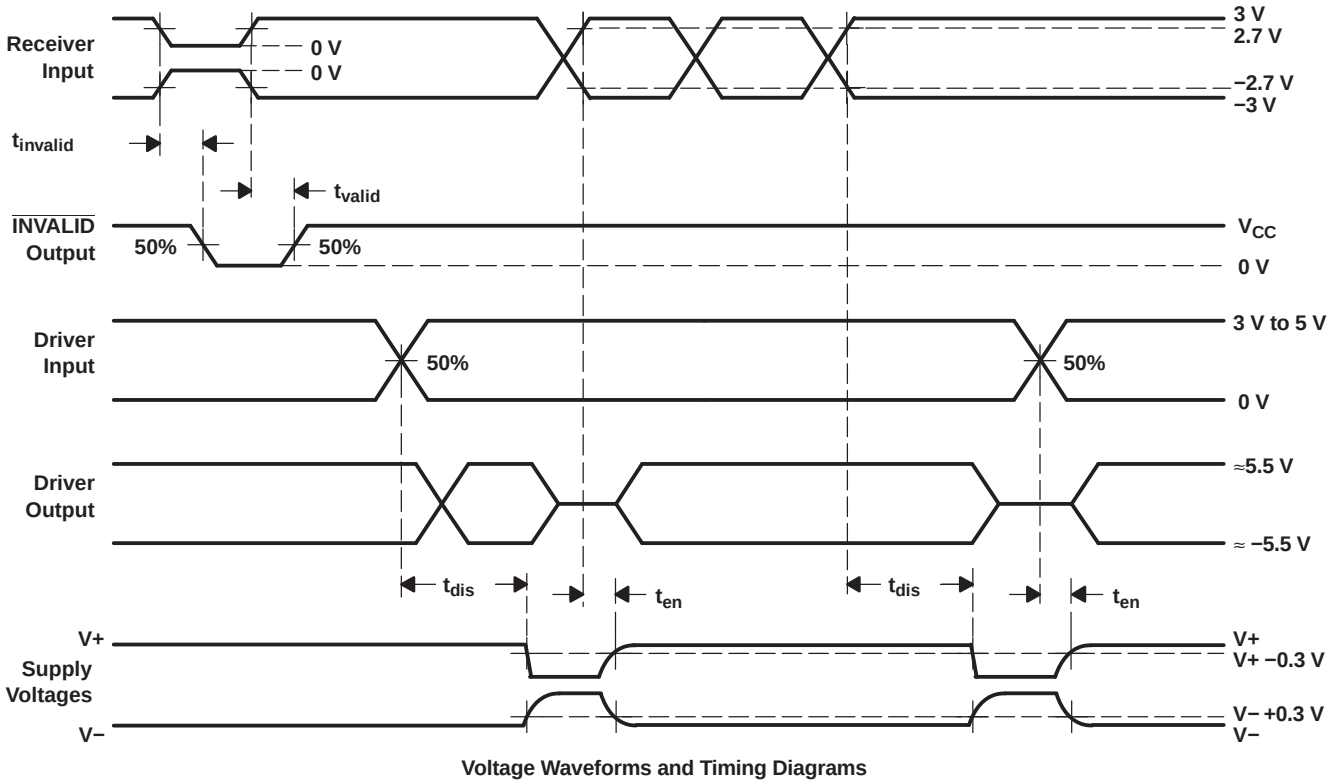


TEST CIRCUIT



† Auto-powerdown plus disables drivers and reduces supply current to 1 µA.

NOTES: A. C_L includes probe and jig capacitance.
B. The pulse generator has the following characteristics: PRR = 5 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

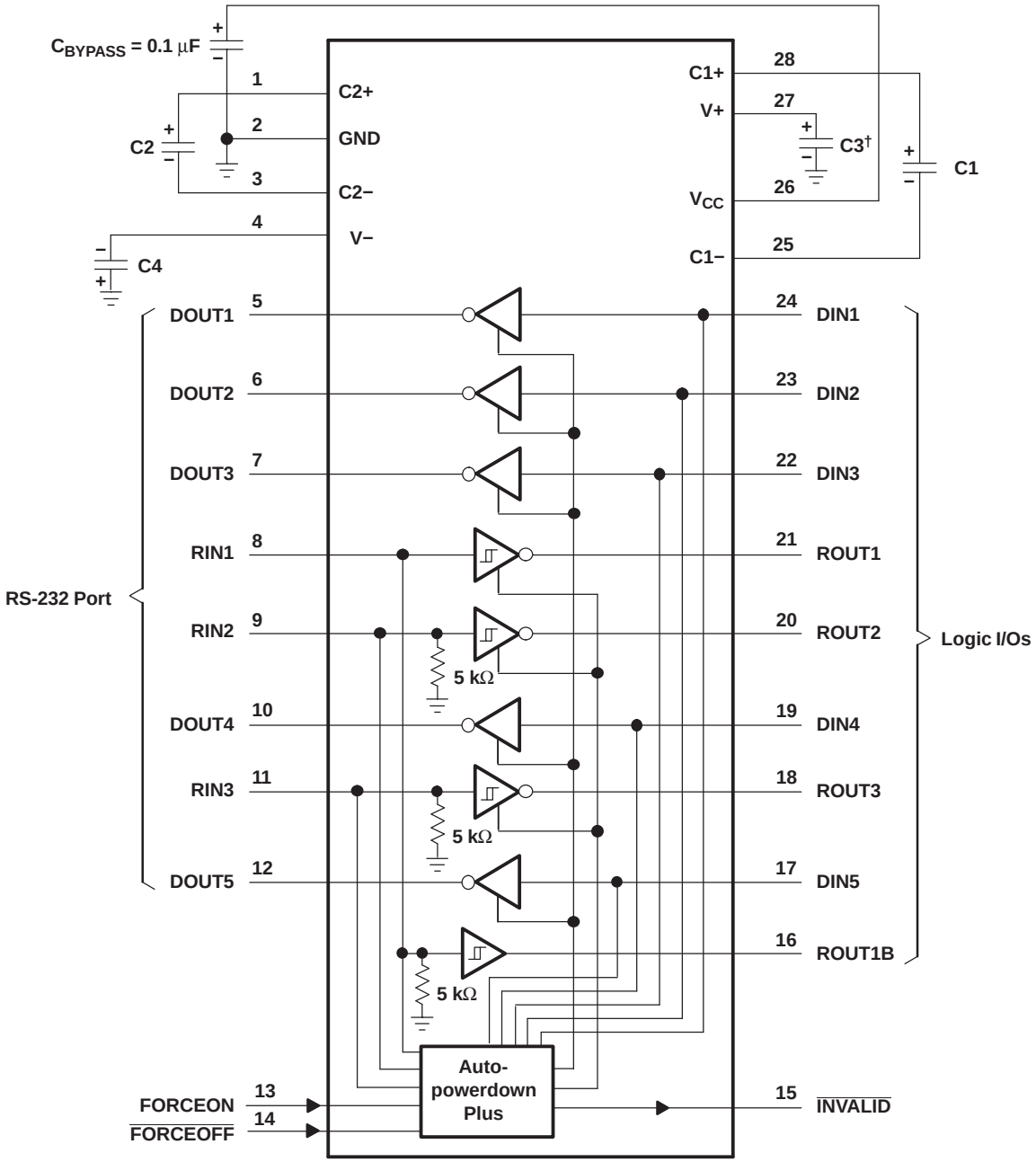


Voltage Waveforms and Timing Diagrams

Figure 5. INVALID Propagation-Delay Times and Supply-Enabling Time

PRODUCT PREVIEW

APPLICATION INFORMATION



V_{CC} vs CAPACITOR VALUES

V_{CC}	C1	C2, C3, and C4
3.3 V ± 0.15 V	0.1 µF	0.1 µF
3.3 V ± 0.3 V	0.22 µF	0.22 µF
5 V ± 0.5 V	0.047 µF	0.33 µF
3 V to 5.5 V	0.22 µF	1 µF

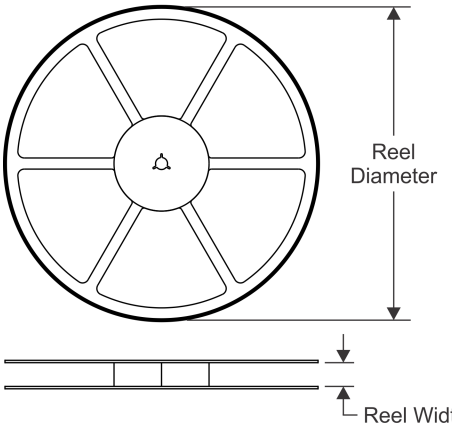
† C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.
B. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

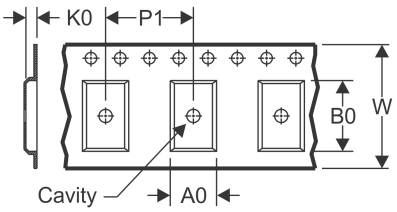
Figure 6. Typical Operating Circuit and Capacitor Values

TAPE AND REEL INFORMATION

REEL DIMENSIONS

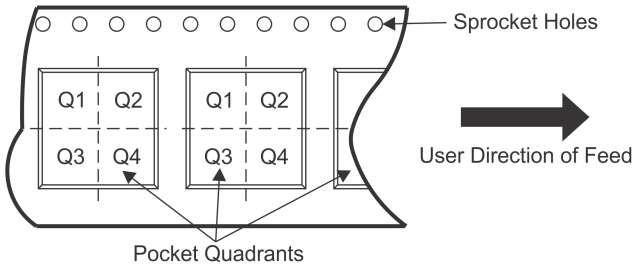


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

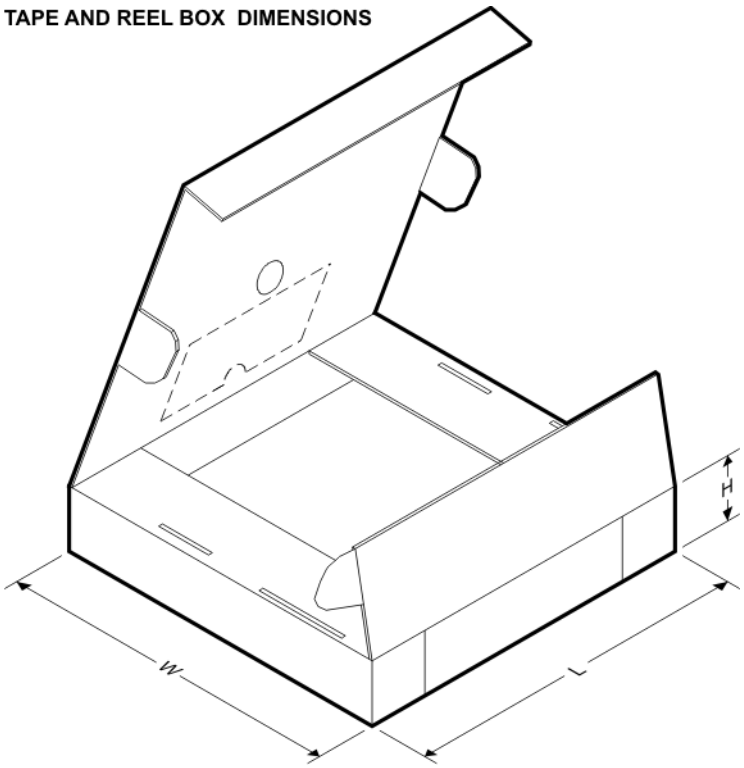
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3238EDBR	SSOP	DB	28	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN65C3238EDWR	SOIC	DW	28	1000	330.0	32.4	11.35	18.67	3.1	16.0	32.0	Q1
SN75C3238EDBR	SSOP	DB	28	2000	330.0	16.4	8.2	10.5	2.5	12.0	16.0	Q1
SN75C3238EDWR	SOIC	DW	28	1000	330.0	32.4	11.35	18.67	3.1	16.0	32.0	Q1

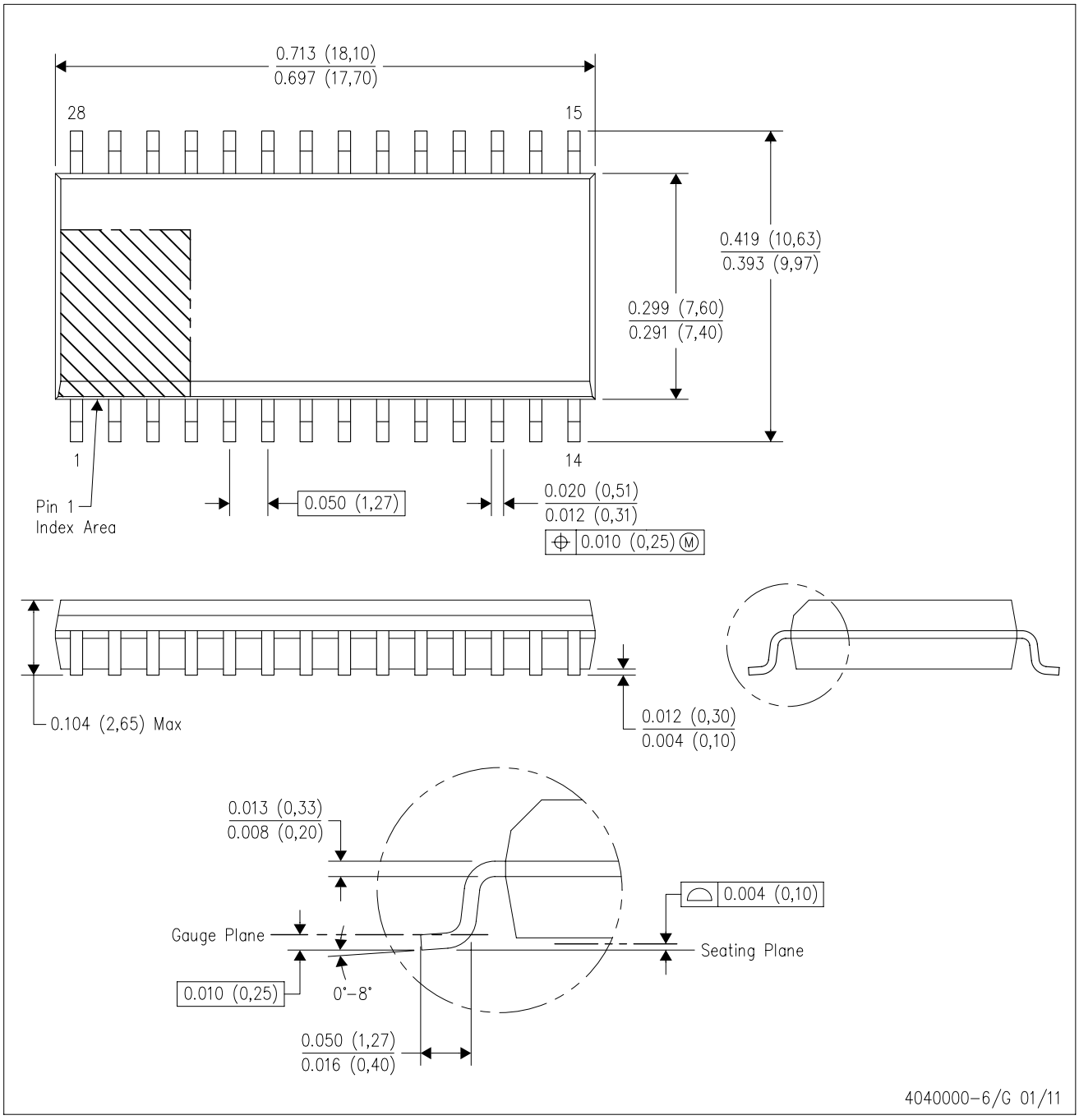
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

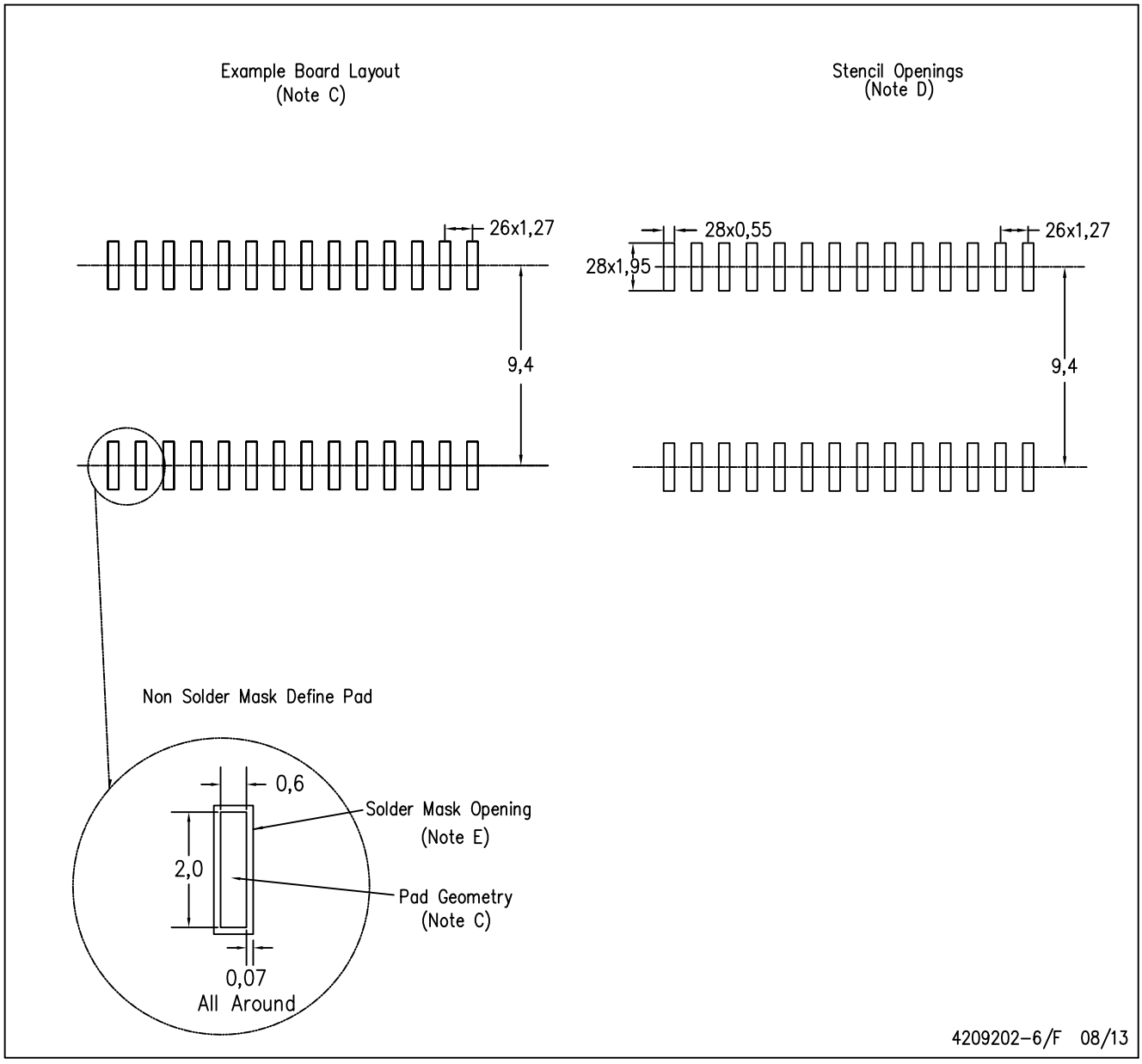
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3238EDBR	SSOP	DB	28	2000	853.0	449.0	35.0
SN65C3238EDWR	SOIC	DW	28	1000	350.0	350.0	66.0
SN75C3238EDBR	SSOP	DB	28	2000	853.0	449.0	35.0
SN75C3238EDWR	SOIC	DW	28	1000	350.0	350.0	66.0

DW (R–PDSO–G28) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–013 variation AE.

DW (R–PDSO–G28) PLASTIC SMALL OUTLINE



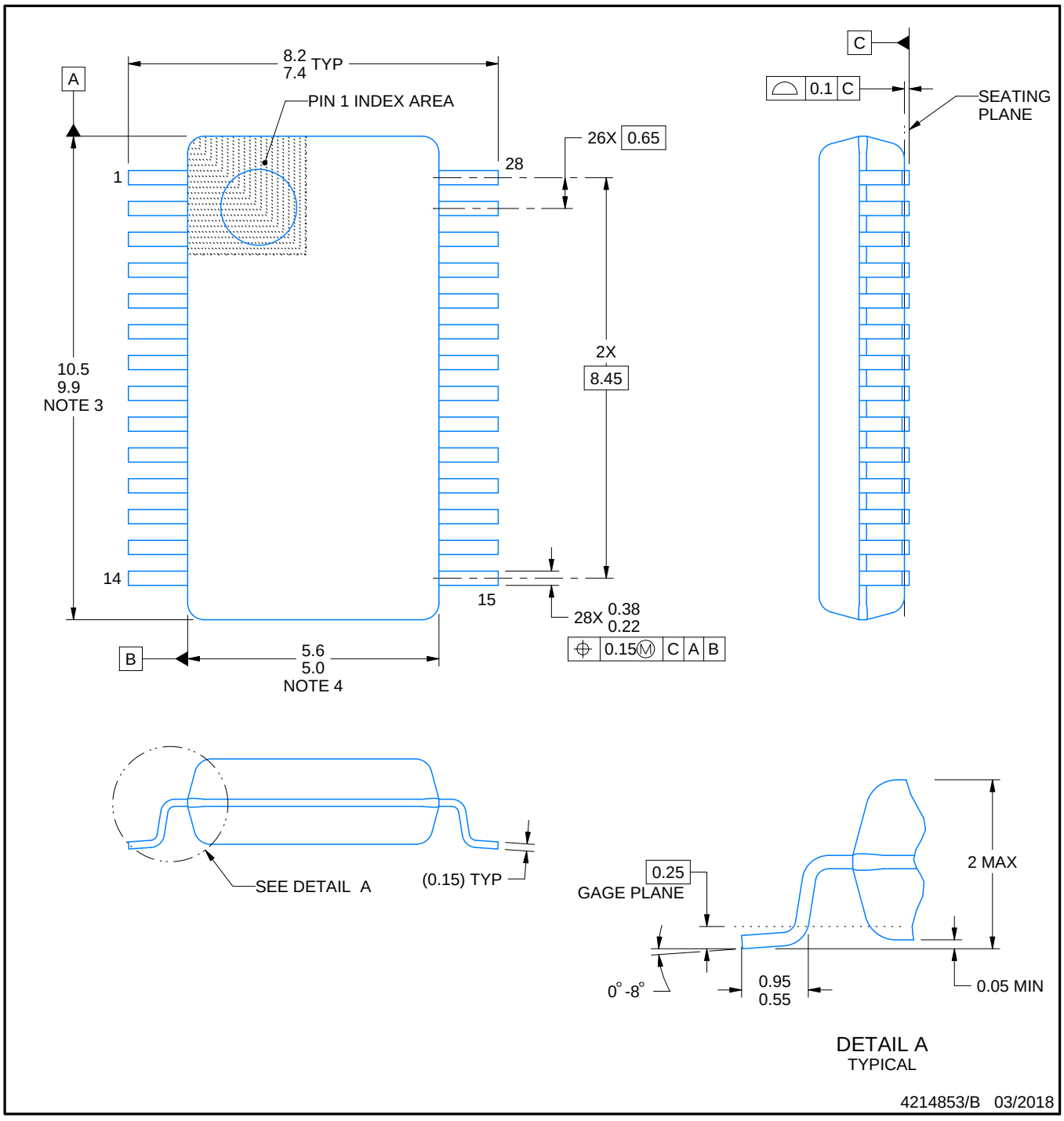
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Refer to IPC7351 for alternate board design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PACKAGE OUTLINE

DB0028A

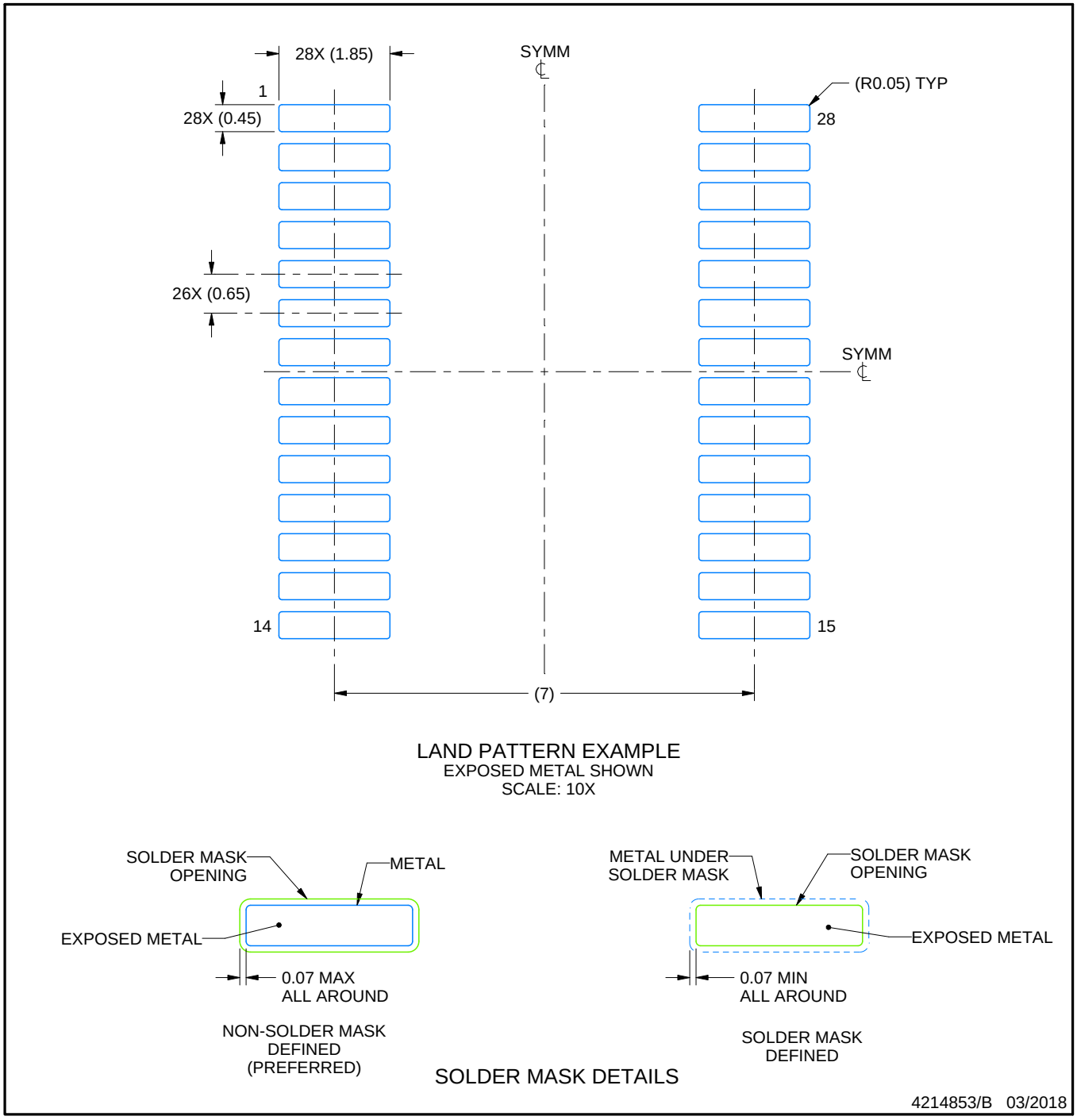
SSOP - 2 mm max height

SMALL OUTLINE PACKAGE



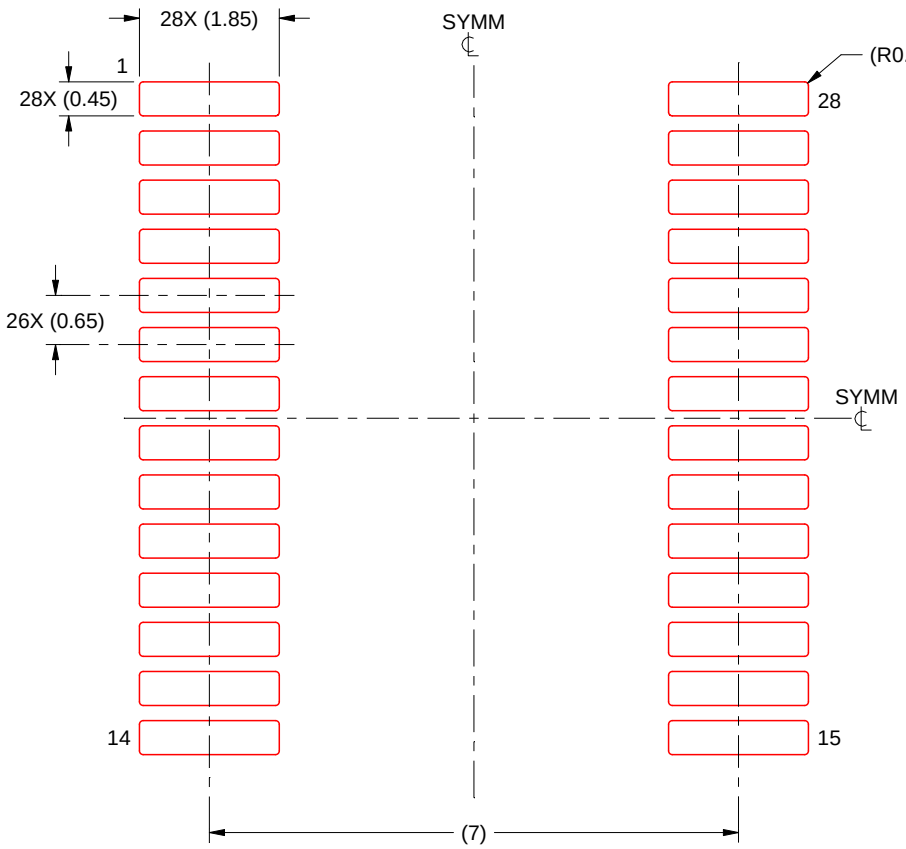
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-150.



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4214853/B 03/2018

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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